

S.N. 09/550,990

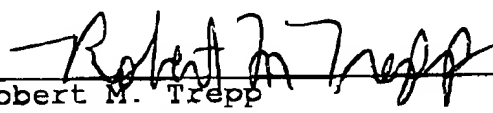
The Abstract is objected to because lines 8-11 refers to purported merits of the claimed invention. The Abstract merely specifies the problem solved. Applicant will delete or change lines 8-11 in a subsequent amendment if the examiner continues the objection. It is respectfully submitted that the abstract is acceptable.

Claims 30 and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kudoh in view of US patent No. 4,521,446 to Coleman, Jr. et al. Kudoh does not teach a gate dielectric layer comprising TiO_2 . Coleman, Jr. et al. teaches the addition of TiO_2 over a very thin silicon dioxide gate dielectric to plug pinhole defects in the oxide. Claim 30, line 7 recites "a gate dielectric of local reacted metal". Coleman, Jr. et al. does not show or suggest a gate dielectric of local reacted metal.

Claim 33 which contains all limitations of claim 30 further recites TiO_2 . The discussions submitted for claim 30 are herein incorporated for claim 33. It is respectfully submitted that claims 30 and 33 are patentable over Kudoh in view of Coleman, Jr. et al.

Further favorable action and allowance of the claims is earnestly requested.

Respectfully submitted,
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by 
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YOR911996-0118

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

Claims 9-12, 22, 23, 31, 32, 37-43, and 58-64. have been
cancelled.

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